

FEATURES

- n - Channel
- High Switching Speed
- Low Forward Voltage Drop
- Isolated Base

APPLICATIONS

- PWM Motor Control
- UPS

The Powerline range of modules includes half bridge, chopper, bi-directional, dual and single switch configurations covering voltages from 600V to 3300V and currents up to 3600A.

The DIM500BSS06-S000 is a single switch 600V n channel enhancement mode insulated gate bipolar transistor (IGBT) module. The module is suitable for a variety of medium voltage applications in motor drives and power conversion.

The IGBT has a wide reverse bias safe operating area (RBSOA) for ultimate reliability in demanding applications.

These modules incorporate electrically isolated base plates and low inductance construction enabling circuit designers to optimise circuit layouts and utilise earthed heat sinks for safety.

Typical applications include dc motor drives, ac pwm drives and ups systems.

ORDERING INFORMATION

Order as:

DIM500BSS06-S000

Note: When ordering, use complete part number.

KEY PARAMETERS

V_{CES} 600V

$V_{CE(sat)}$ * (typ) 2.1V

I_C (max) 500A

$I_{C(PK)}$ (max) 1000A

*(measured at the power busbars and not the auxiliary terminals)

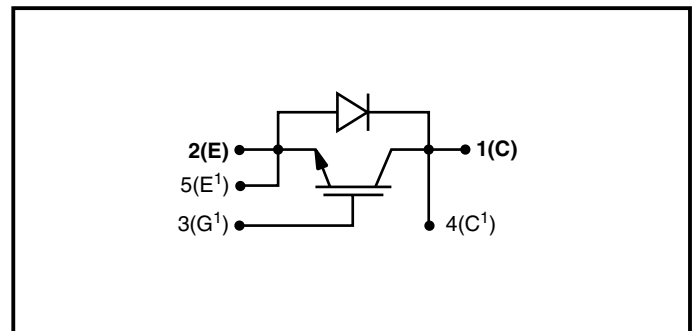


Fig. 1 Single switch circuit diagram



Outline type code: B

(See package details for further information)

Fig. 2 Module outline

ABSOLUTE MAXIMUM RATINGS - PER ARM

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0\text{V}$	600	V
V_{GES}	Gate-emitter voltage	-	± 20	V
I_C	Continuous collector current	$T_{case} = 65^{\circ}\text{C}$	500	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 95^{\circ}\text{C}$	1000	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	2907	W
I^2t	Diode I^2t value	$V_R = 0$, $t_p = 10\text{ms}$, $T_{vj} = 125^{\circ}\text{C}$	TBD	kA^2s
V_{isol}	Isolation voltage - per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2.5	kV

THERMAL AND MECHANICAL RATINGS

Internal insulation: Al_2O_3 Clearance: 11mm
 Baseplate material: Cu CTI (Critical Tracking Index): 425
 Creepage distance: 20mm

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - transistor	Continuous dissipation - junction to case	-	-	43	°C/kW
$R_{th(j-c)}$	Thermal resistance - diode	Continuous dissipation - junction to case	-	-	81	°C/kW
$R_{th(c-h)}$	Thermal resistance - case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	15	°C/kW
T_j	Junction temperature	Transistor	-	-	150	°C
		Diode	-	-	125	°C
T_{stg}	Storage temperature range	-	-40	-	125	°C
-	Screw torque	Mounting - M6	3	-	5	Nm
		Electrical connections - M3	2.5	-	5	Nm
		Electrical connections - M4	1.1		2	Nm

ELECTRICAL CHARACTERISTICS

$T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{CES}	Collector cut-off current	$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = V_{\text{CES}}$	-	-	3	mA
		$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = V_{\text{CES}}, T_{\text{case}} = 125^{\circ}\text{C}$	-	-	15	mA
I_{GES}	Gate leakage current	$V_{\text{GE}} = \pm 20\text{V}, V_{\text{CE}} = 0\text{V}$	-	-	3	μA
$V_{\text{GE(TH)}}$	Gate threshold voltage	$I_{\text{C}} = 20\text{mA}, V_{\text{GE}} = V_{\text{CE}}$	4.5	5.5	7.5	V
$V_{\text{CE(sat)}}^{\dagger}$	Collector-emitter saturation voltage	$V_{\text{GE}} = 15\text{V}, I_{\text{C}} = 375\text{A}$	-	2.1	2.6	V
		$V_{\text{GE}} = 15\text{V}, I_{\text{C}} = 375\text{A}, T_{\text{case}} = 125^{\circ}\text{C}$	-	2.3	2.8	V
I_{F}	Diode forward current	DC	-	-	500	A
I_{FM}	Diode maximum forward current	$t_{\text{p}} = 1\text{ms}$	-	-	1000	A
$V_{\text{F}}^{\dagger}$	Diode forward voltage	$I_{\text{F}} = 50\text{A}$	-	1.5	1.8	V
		$I_{\text{F}} = 500\text{A}, T_{\text{case}} = 125^{\circ}\text{C}$	-	1.5	1.8	V
C_{ies}	Input capacitance	$V_{\text{CE}} = 25\text{V}, V_{\text{GE}} = 0\text{V}, f = 1\text{MHz}$	-	54	-	nF
L_{M}	Module inductance	-	-	20	-	nH
R_{INT}	Internal transistor resistance - per arm	-	-	0.23		m Ω

Note:

$\dagger$ Measured at the power busbars and not the auxiliary terminals.

L^* is the circuit inductance + L_{M}

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(off)}$	Turn-off delay time	$I_C = 500\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 300\text{V}$ $R_{G(ON)} = R_{G(OFF)} = 4.7\Omega$ $L \sim 100\text{nH}$	-	600	-	ns
t_f	Fall time		-	250	-	ns
E_{OFF}	Turn-off energy loss		-	45	-	mJ
$t_{d(on)}$	Turn-on delay time		-	490	-	ns
t_r	Rise time		-	150	-	ns
E_{ON}	Turn-on energy loss		-	30	-	mJ
Q_g	Gate charge		-	4	-	μC
Q_{rr}	Diode reverse recovery charge	$I_F = 500\text{A}, V_R = 300\text{V},$ $di_F/dt = 2800\text{A}/\mu\text{s}$	-	30	-	μC
I_{rr}	Diode reverse current		-	240	-	A
E_{REC}	Diode reverse recovery energy		-	9	-	mJ

$T_{case} = 125^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(off)}$	Turn-off delay time	$I_C = 500\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 300\text{V}$ $R_{G(ON)} = R_{G(OFF)} = 4.7\Omega$ $L \sim 100\text{nH}$	-	650	-	ns
t_f	Fall time		-	500	-	ns
E_{OFF}	Turn-off energy loss		-	65	-	mJ
$t_{d(on)}$	Turn-on delay time		-	550	-	ns
t_r	Rise time		-	150	-	ns
E_{ON}	Turn-on energy loss		-	50	-	mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 500\text{A}, V_R = 300\text{V},$ $di_F/dt = 2800\text{A}/\mu\text{s}$	-	40	-	μC
I_{rr}	Diode reverse current		-	265	-	A
E_{REC}	Diode reverse recovery energy		-	10	-	mJ

TYPICAL CHARACTERISTICS

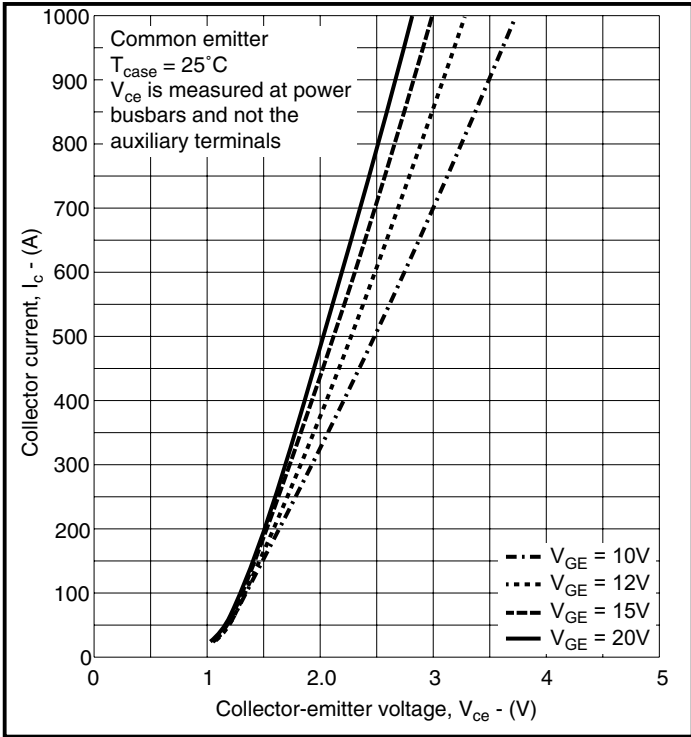


Fig.3 Typical output characteristics

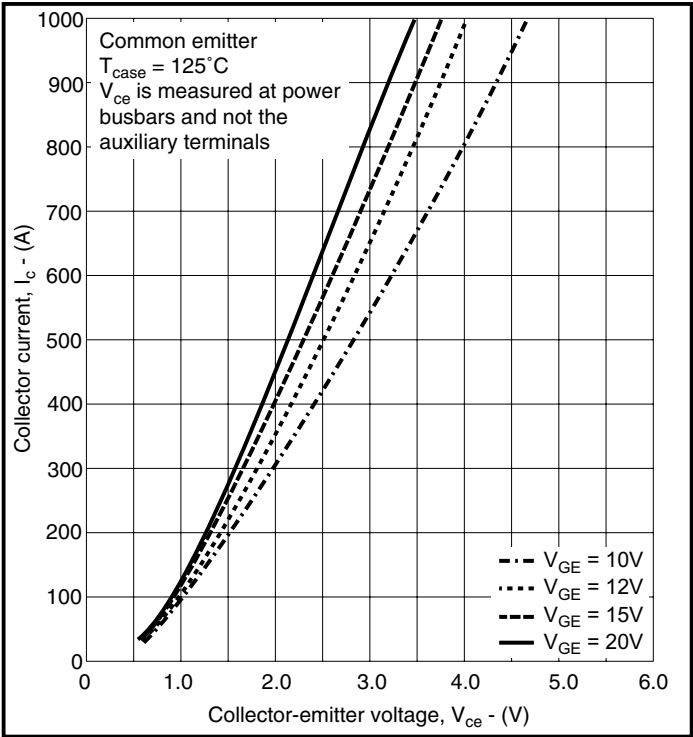


Fig.4 Typical output characteristics

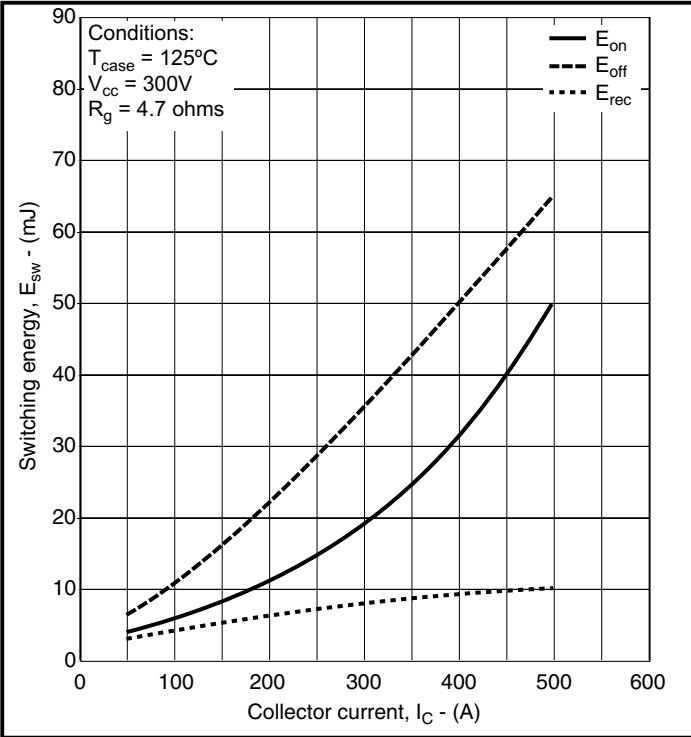


Fig.4 Typical switching energy vs collector current

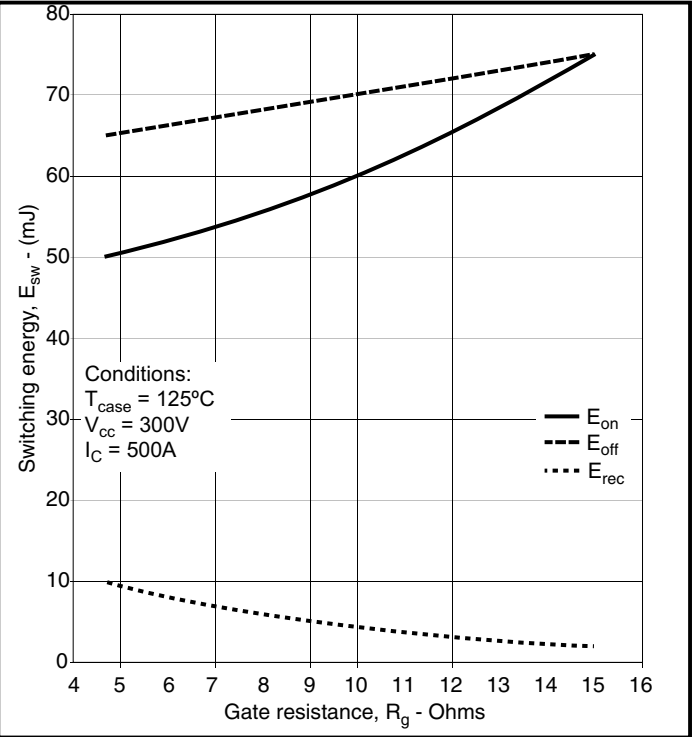
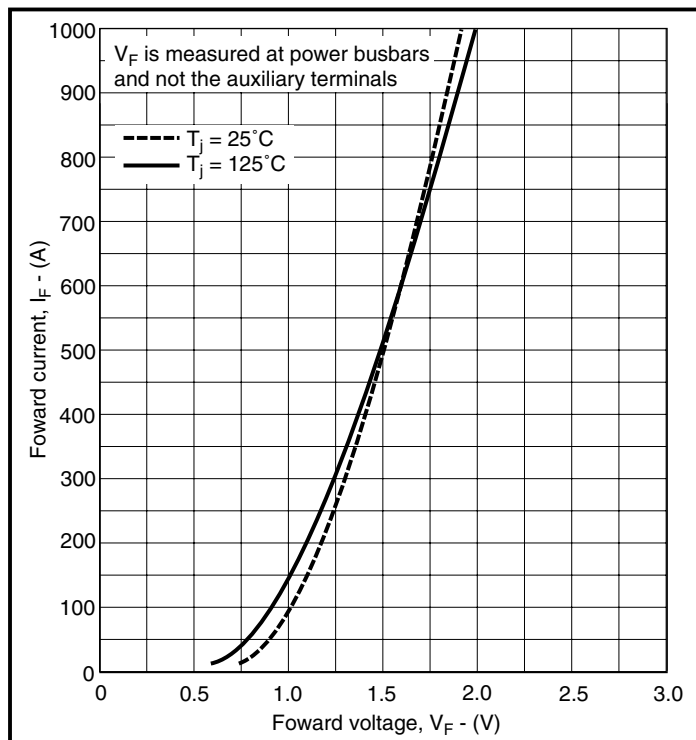
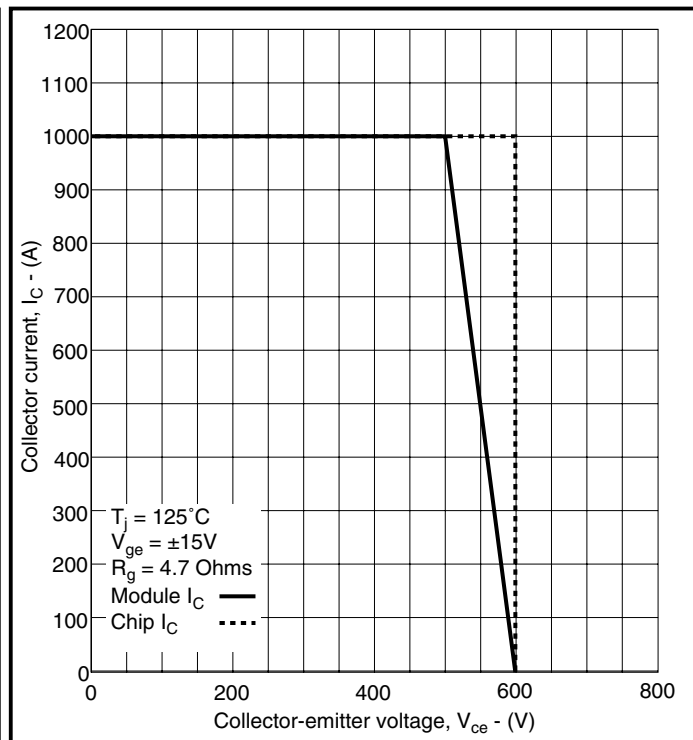
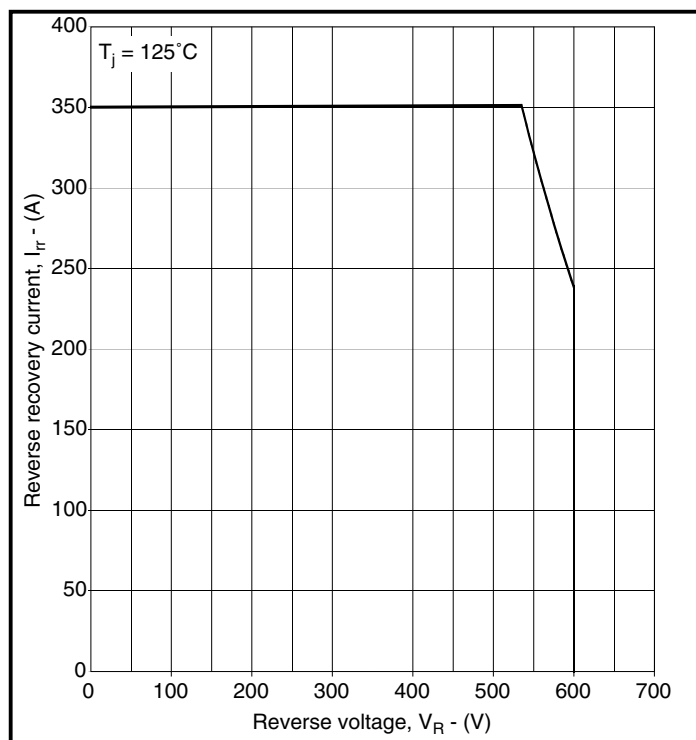
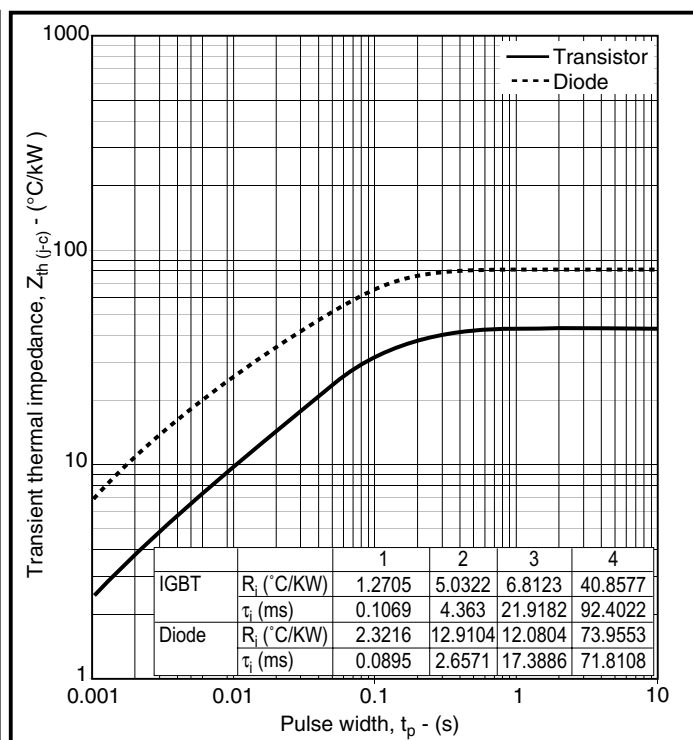


Fig.5 Typical switching energy vs gate resistance


Fig.6 Diode typical forward characteristics

Fig.7 Reverse bias safe operating area

Fig.7 Diode reverse bias safe operating area

Fig.8 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise.
DO NOT SCALE.

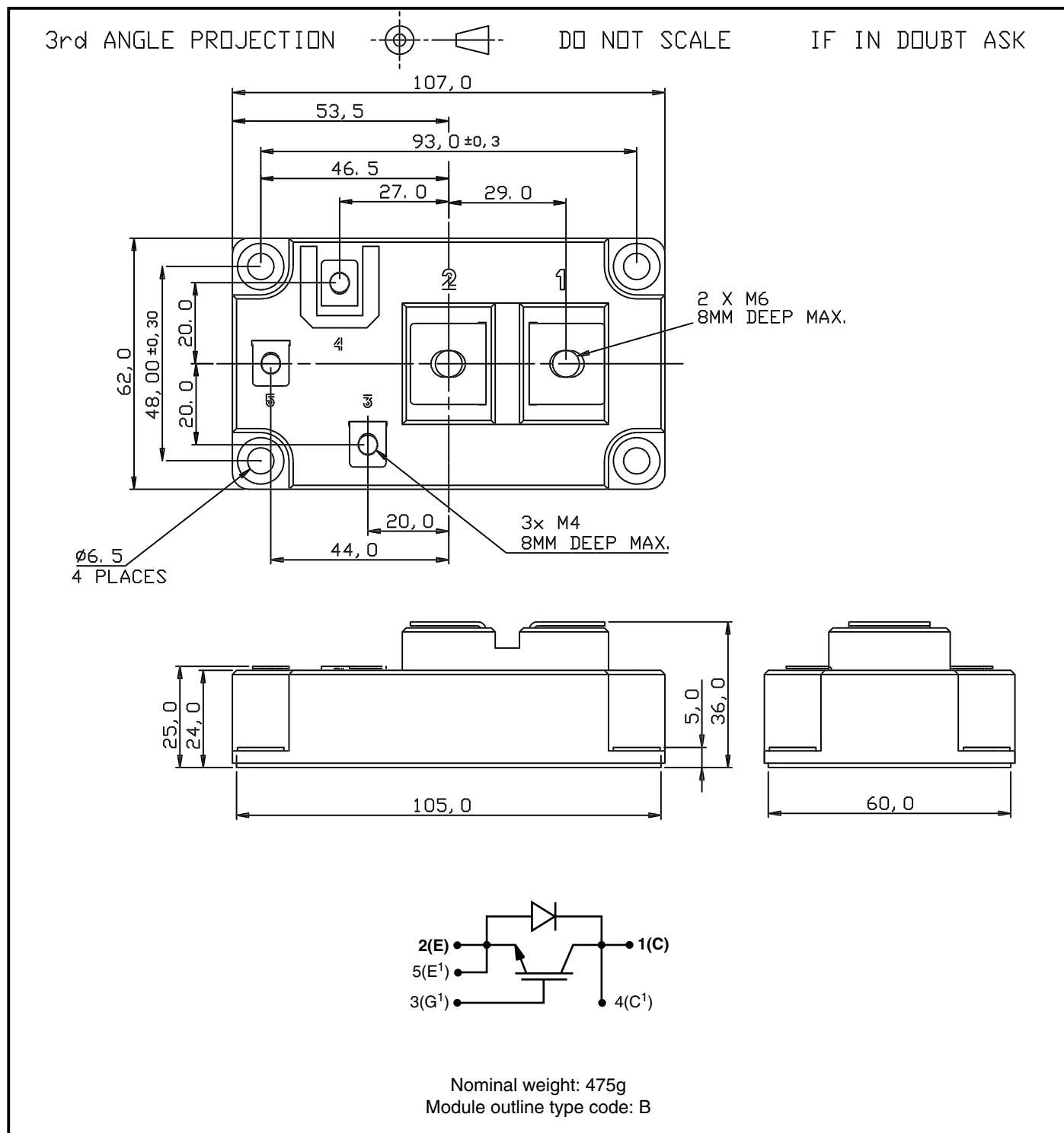


Fig. 15 Package details

POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



<http://www.dynexsemi.com>

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